

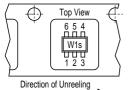
NPN / PNP Silicon AF Transistor Array

- High breakdown voltage
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated NPN/PNP Transistor in one package
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

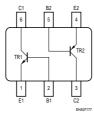




Tape loading orientation



Marking on SC74 package (for example W1s) corresponds to pin 1 of device



	Marking	Pi	in Conf	figurati	on	Package	
reeling	SC74_Tape						
2 3	Position in tape: pin 1 opposite of feed hole side	EHA07	177				

Type	Marking		Р	Package				
SMBTA06UPN	s2P	1=E	2=B	3=C	4=E	5=B	6=C	SC74

waximum	Ratings
Parameter	•

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	80	V
Collector-base voltage	V_{CBO}	80	
Emitter-base voltage	V _{EBO}	4	
Collector current	I _C	500	mA
Peak collector current, $t_p \le 10 \text{ ms}$	I _{CM}	1	Α
Base current	l _B	100	mA
Peak base current	l _{BM}	200	
Total power dissipation-	P _{tot}	330	mW
<i>T</i> _S ≤ 115 °C			
Junction temperature	$ T_i $	150	°C
Storage temperature	T _{stq}	-65 150	



Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 105	K/W

Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol		Values		Unit	
		min.	typ.	max.		
DC Characteristics				•		
Collector-emitter breakdown voltage	V _{(BR)CEO}	80	-	-	V	
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0						
Collector-base breakdown voltage	V _{(BR)CBO}	80	-	-		
$I_{\rm C}$ = 100 μ A, $I_{\rm E}$ = 0	, ,					
Emitter-base breakdown voltage	$V_{(BR)EBO}$	4	-	-		
$I_{\rm E}$ = 10 μ A, $I_{\rm C}$ = 0						
Collector-base cutoff current	I _{CBO}				μΑ	
$V_{\rm CB}$ = 80 V, $I_{\rm E}$ = 0		-	-	0.1		
V_{CB} = 80 V, I_{E} = 0 , T_{A} = 150 °C		-	-	20		
Collector-emitter cutoff current	I _{CEO}	-	-	100	nA	
$V_{CE} = 60 \text{ V}, I_{B} = 0$						
DC current gain ²⁾	h _{FE}				-	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 1 V		100	_	_		
$I_{\rm C}$ = 100 mA, $V_{\rm CE}$ = 1 V		100	-	-		
Collector-emitter saturation voltage ²⁾	V _{CEsat}	-	-	0.25	V	
$I_{\rm C}$ = 100 mA, $I_{\rm B}$ = 10 mA						
Base-emitter voltage ²⁾	V _{BE(ON)}	-	-	1.2		
$I_{\rm C}$ = 100 mA, $V_{\rm CE}$ = 1 V						
AC Characteristics						
Transition frequency	f _T	-	100	-	MHz	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 5 V, f = 20 MHz						
Collector-base capacitance	C _{cb}	-	7	-	pF	
$V_{\text{CB}} = 10 \text{ V}, f = 1 \text{ MHz}$						

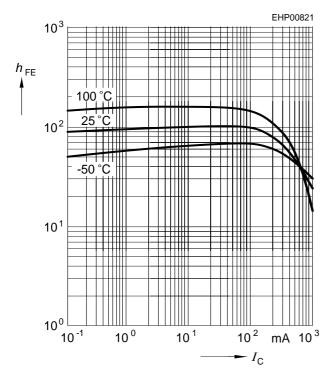
 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

 $^{^{2}}$ Pulse test: t < 300 μ s; D < 2%



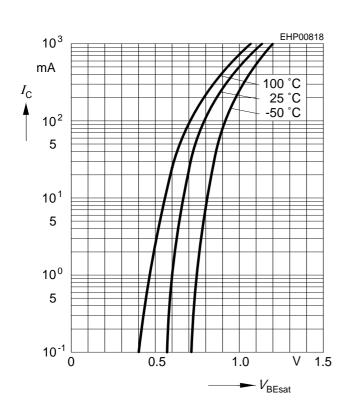
DC current gain $h_{FE} = f(I_C)$

$$V_{CE} = 1 \text{ V}$$



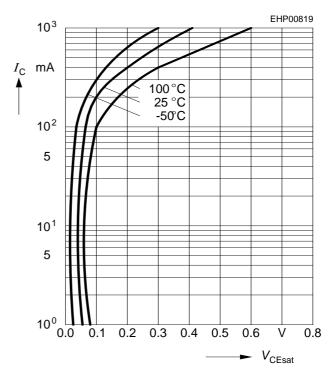
Base-emitter saturation voltage

$$I_{\rm C} = f(V_{\rm BEsat}), h_{\rm FE} = 10$$



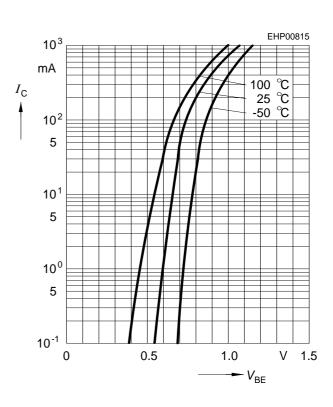
Collector-emitter saturation voltage

$$I_{\text{C}} = f(V_{\text{CEsat}}), h_{\text{FE}} = 10$$



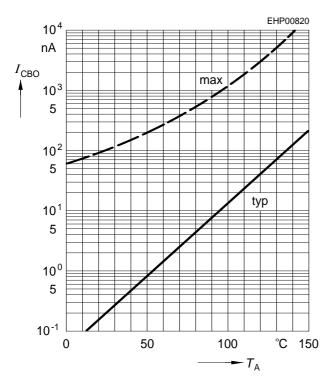
Collector current $I_{C} = f(V_{BE})$

$$V_{CE} = 1V$$

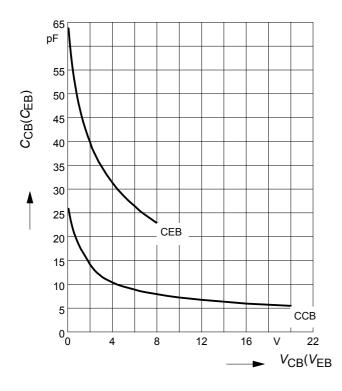




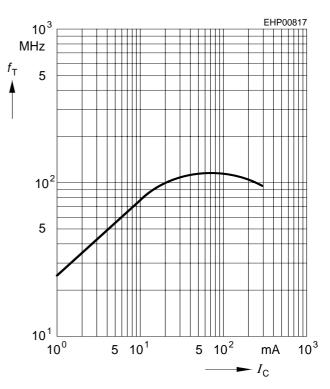
Collector cutoff current $I_{CBO} = f(T_A)$ $V_{CBO} = 80 \text{ V}$



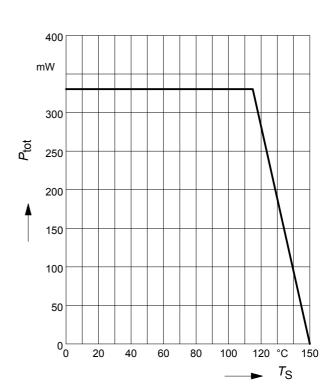
Collector-base capacitance $C_{cb} = f(V_{CB})$ Emitter-base capacitance $C_{eb} = f(V_{EB})$



Transition frequency $f_T = f(I_C)$ V_{CE} = parameter in V, f = 2 GHz



Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$



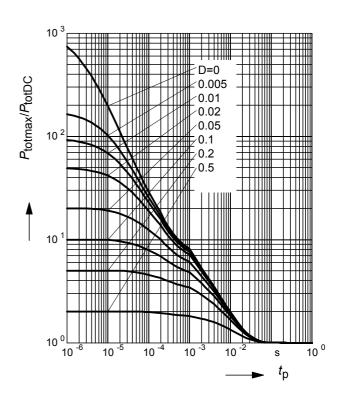


Permissible Pulse Load $R_{thJS} = f(t_p)$

10 ³ K/W 10 ² 10 ¹ 10 ⁰ 10 ⁰ 10 ⁰ 10 ⁰ 10 ⁰ 10 ¹ 10 ⁰ 10 ¹ 10 ¹

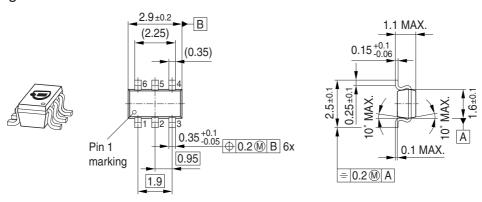
Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$$

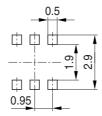




Package Outline

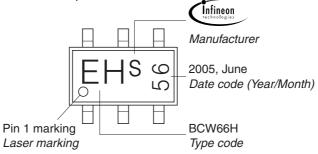


Foot Print



Marking Layout (Example)

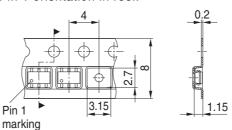
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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